

General Description

The WSD13N10TDN33 uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V.

This device is suitable for use as a Battery protection or in other Switching application.

Features

- 100% UIS + R_g Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)
- Moisture Sensitivity Level MSL1 (per JEDEC J-STD-020D)

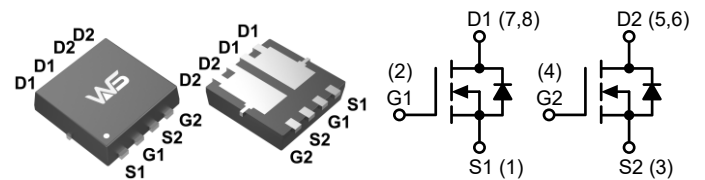
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D
100V	70m Ω	15A

Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

DFN3X3-8L Pin Configuration



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$, Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		100	V
V_{GS}	Gate-Source Voltage		± 20	
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$	15	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	15	
		$T_C=100^\circ\text{C}$	9.4	
I_{DM}^2	Pulse Drain Current	$T_C=25^\circ\text{C}$	45	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	23	W
		$T_C=100^\circ\text{C}$	9	
$R_{\theta JA}^4$	Thermal Resistance-Junction to Ambient	Steady State	95	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance-Junction to Case		5.5	
I_{AS}^3	Avalanche Current, Single pulse	L=0.5mH	8	A
E_{AS}^3	Avalanche Energy, Single pulse	L=0.5mH	16	mJ
T_{STG}	Storage Temperature Range		-55 to 150	$^\circ\text{C}$
T_J	Maximum Junction Temperature		150	

Electrical Characteristics ($T_A=25^\circ\text{C}$, Unless Otherwise Noted)

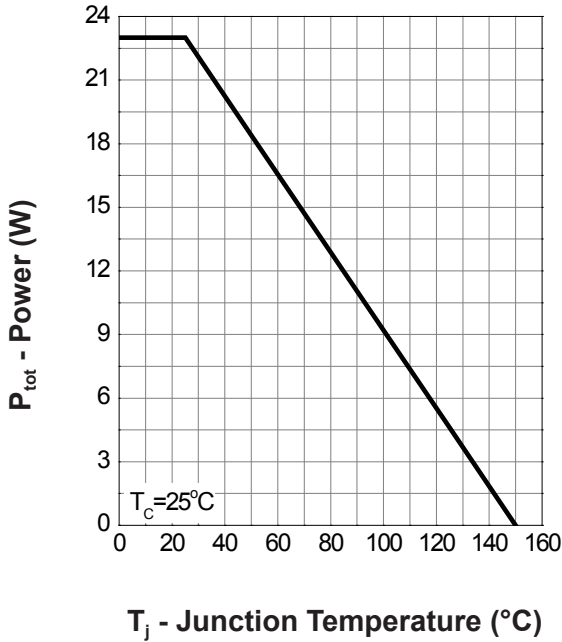
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=80V, V_{GS}=0V$	---	---	1.0	μA
		$T_J=85^\circ\text{C}$	---	---	30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_{DS}=250\mu A$	1.0	1.7	2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
$R_{DS(on)}^5$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=7A$	---	70	82	m Ω
		$V_{GS}=4.5V, I_D=4A$	---	85	107	
Diode Characteristics						
V_{SD}^5	Diode Forward Voltage	$I_{SD}=7A, V_{GS}=0V$	---	0.8	1.3	V
t_{rr}	Reverse Recovery Time	$I_{DS}=7A, di_{SD}/dt=100A/\mu s$	---	30	---	ns
Q_{rr}	Reverse Recovery Charge		---	40	---	nC
Dynamic Characteristics ⁶						
R_g	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1.0\text{MHz}$	---	1.5	---	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=50V,$ Frequency=1.0MHz	---	390	510	pF
C_{oss}	Output Capacitance		---	72	---	
C_{rss}	Reverse Transfer Capacitance		---	20	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, R_L=30\Omega, I_{DS}=1A,$ $V_{GEN}=10V, R_G=6\Omega$	---	8	13	ns
T_r	Turn-on Rise Time		---	6	10	
$T_{d(off)}$	Turn-off Delay Time		---	13	21	
T_f	Turn-off Fall Time		---	11	18	
Gate Charge Characteristics ⁶						
Q_g	Total Gate Charge	$V_{DS}=50V, V_{GS}=10V, I_{DS}=7A$	---	7.5	11	nC
Q_{gs}	Gate-Source Charge		---	2.4	---	
Q_{gd}	Gate-Drain Charge		---	1.6	---	

Note:

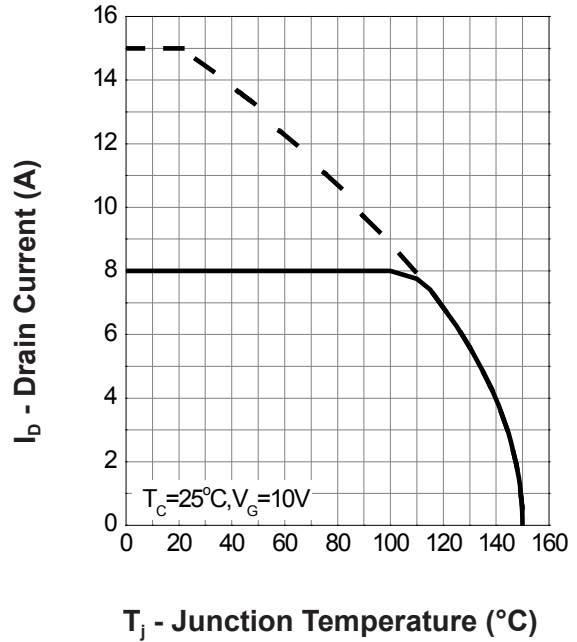
1. Calculated continuous current based on maximum allowable junction temperature. Bonding wire limitation current is 8A.
2. Pulse width limited by max. junction temperature.
3. UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).
4. Surface Mounted on 1in² pad area.
5. Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
6. Guaranteed by design, not subject to production testing.

Typical Characteristics

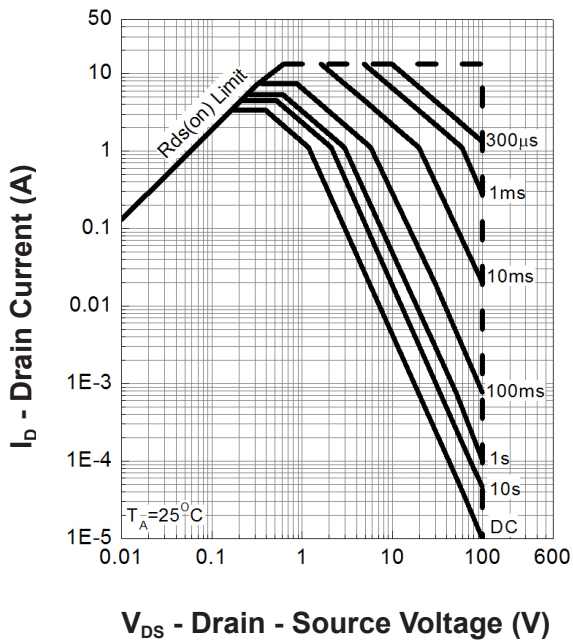
Power Dissipation



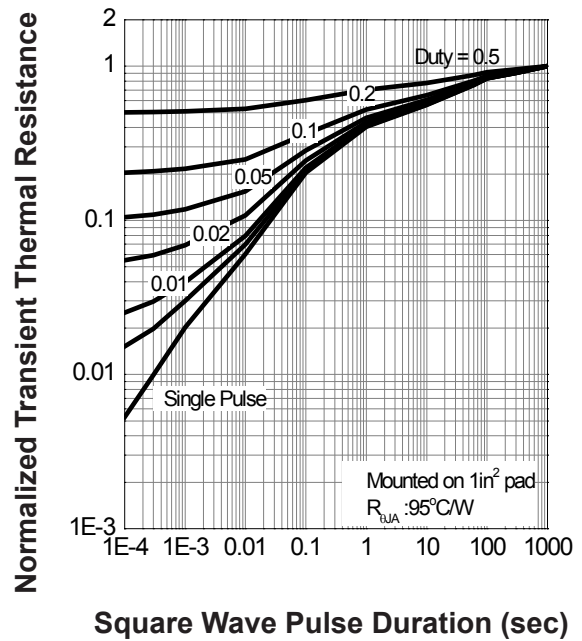
Drain Current



Safe Operation Area

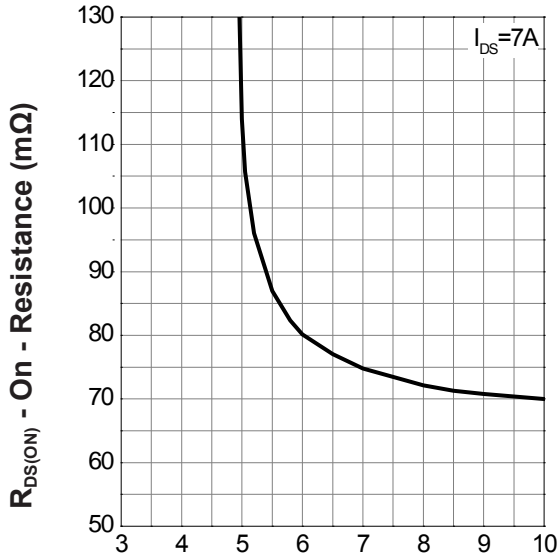


Thermal Transient Impedance



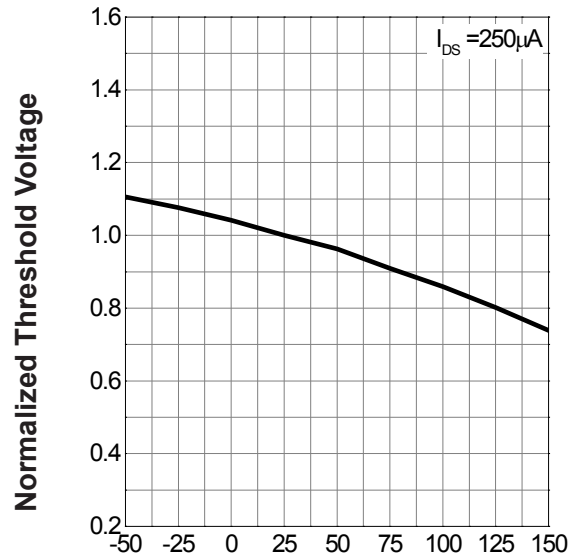
Typical Characteristics (Cont.)

Gate-Source On Resistance



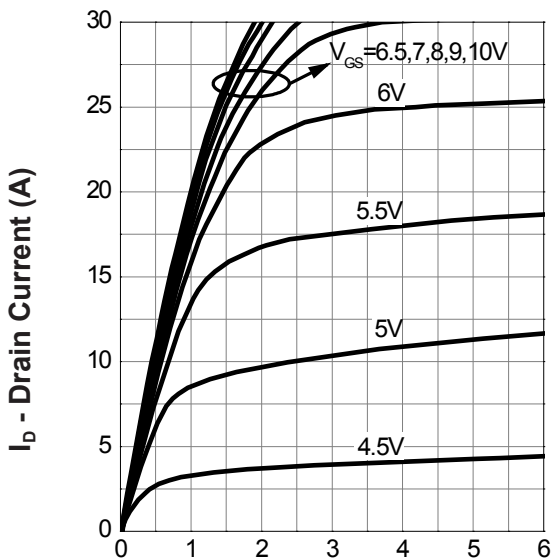
V_{GS} - Gate - Source Voltage (V)

Gate Threshold Voltage



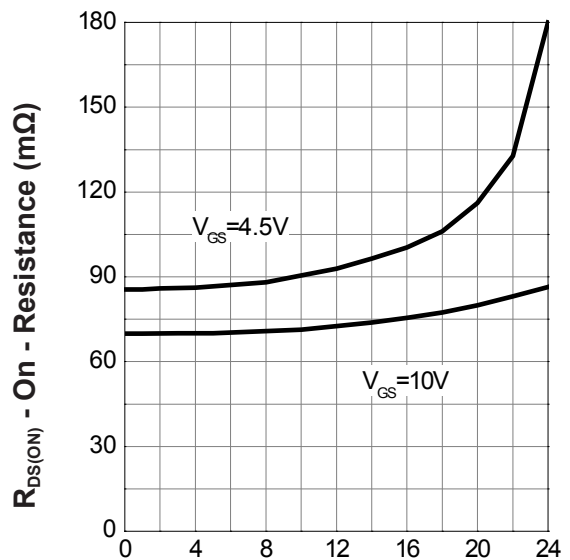
T_J - Junction Temperature (°C)

Output Characteristics



V_{DS} - Drain - Source Voltage (V)

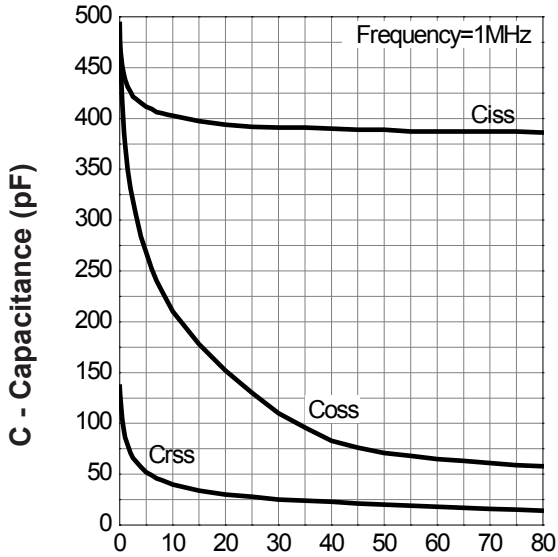
Drain-Source On Resistance



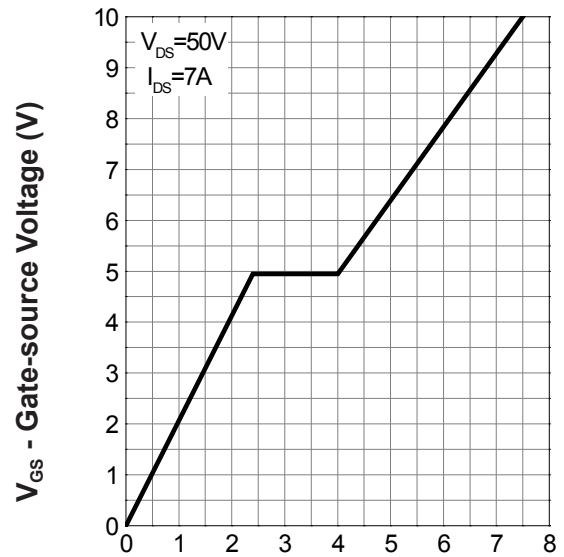
I_D - Drain Current (A)

Typical Characteristics (Cont.)

Capacitance



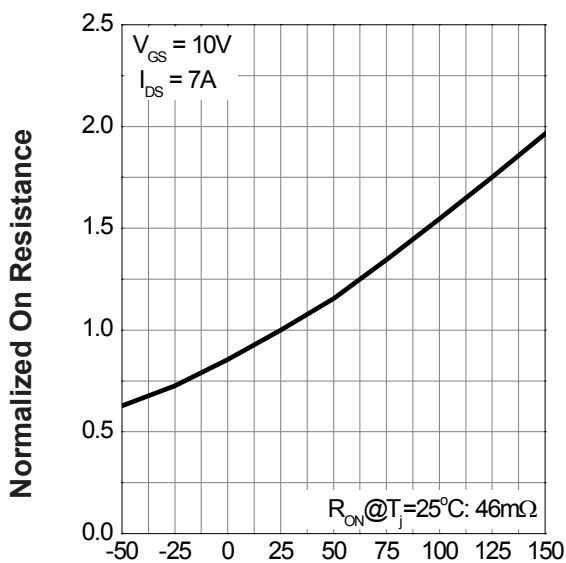
Gate Charge



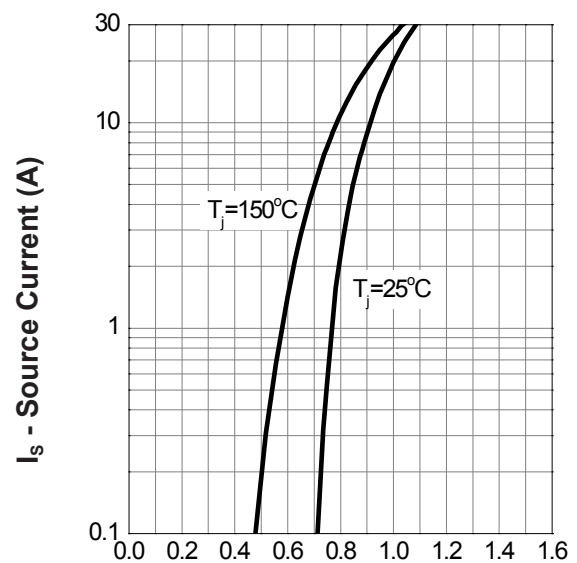
V_{DS} - Drain-Source Voltage (V)

Q_G - Gate Charge (nC)

Drain-Source On Resistance

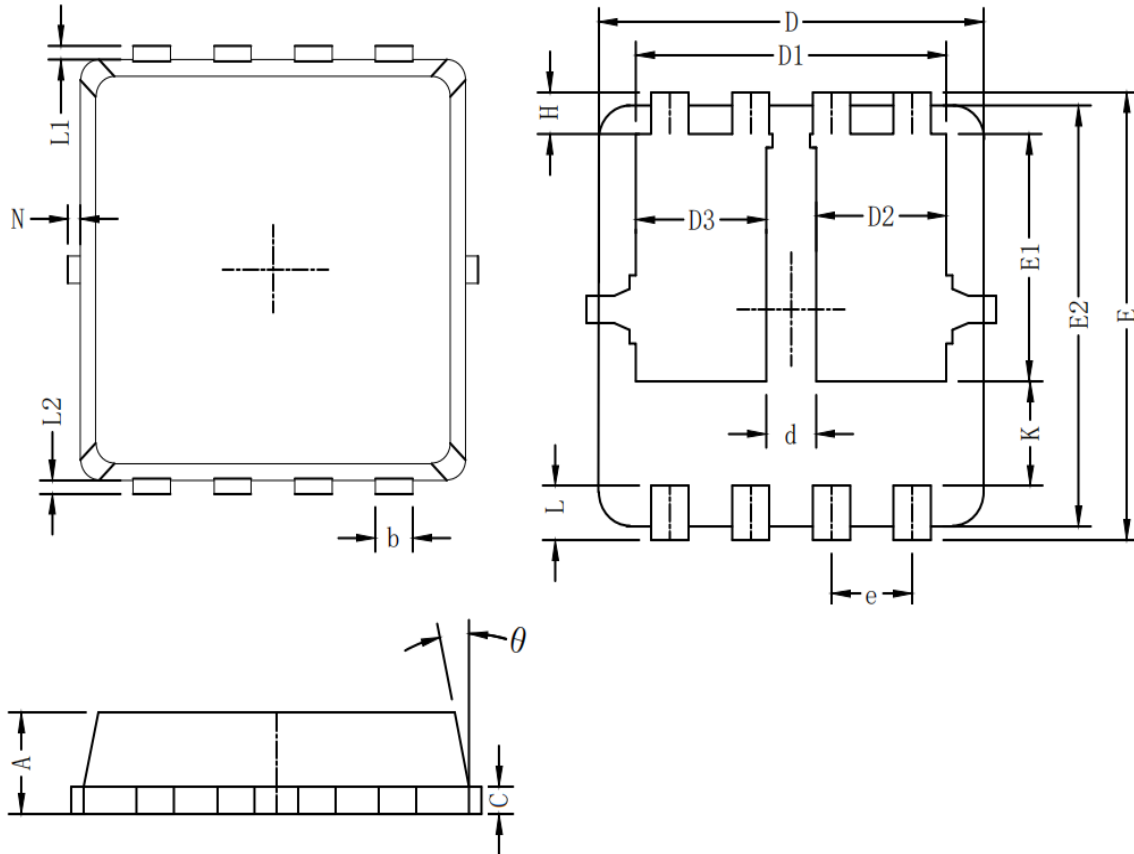


Source-Drain Diode Forward



T_j - Junction Temperature ($^\circ C$)

V_{SD} - Source - Drain Voltage (V)

Packaging information


Symbol	Dim in mm		
	min	typ	max
A	0.6	0.75	0.9
b	0.2	0.3	0.4
C	0.15	0.2	0.25
D	3	3.1	3.2
D1	2.3	2.45	2.6
D2/D3	0.8	1	1.2
E	3.15	3.3	3.45
E1	1.43	1.73	1.93
E2	2.9	3.05	3.2
e	0.65BSC		
H	0.2	0.35	0.5
K	0.57	0.77	0.87
L	0.3	0.4	0.5
L1/L2	0.1REF		
θ	8°	10°	13°
N	0		0.15
d	0.3	0.4	0.5

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